MOS INTEGRATED CIRCUIT μ PD16331

40-BIT AC-PDP DRIVER

The μ PD16331 is a column driver for an AC plasma display panel (PDP) using high breakdown voltage CMOS process. It consists of 40-bit bidirectional shift register, latch circuit and high breakdown voltage CMOS driver blocks. The logic block operates on a 5 V power supply so that it can be connected directly to a microcontroller (CMOS level input). The driver block has high breakdown voltage output of 100 V and ±150 mA MAX. Both the logic block and driver block are constructed by CMOS, which allows operation with low power consumption.

FEATURES

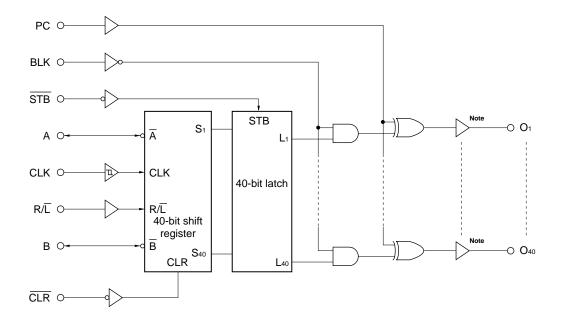
NEC

- High voltage full CMOS process
- High breakdown voltage, high current output (100 V, ±150 mA MAX.)
- 40-bit bidirectional shift register on chip
- Data control by transfer clock (external) and latch
- High speed data transfer capability (fmax. = 16 MHz MIN.; when cascaded)
- Wide operating temperature range (TA = -20 to 85 °C)
- Polarity of all driver outputs can be inverted by PC pins.

ORDERING INFORMATION

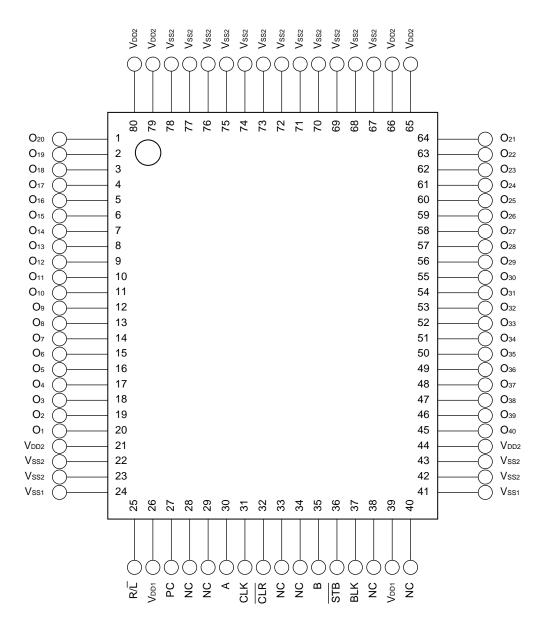
Part Number	Package
μPD16331GF-3B9	80-pin plastic QFP (copper lead frame)

BLOCK DIAGRAM



Note High breakdown voltage CMOS driver

PIN CONFIGURATION (Top View)



Be sure to use all of the VDD1, VDD2, VSS1, and VSS2 pins. Use VSS1 and VSS2 at the same potential. The power should be turned on for VDD1, logic input, and VDD2, in that order and should be turned off in the reverse order.

PIN DESCRIPTION

Pin Symbol	Pin Name	Pin No.	Description
PC	Inverted polarity input	27	PC = H: Polarity of all outputs inverted
BLK	Blanking input	37	BLK = H: All outputs = H or L
STB	Latch strobe input	36	L: Through H: Data retained
A ^{Note}	RIGHT data input	30	When $R/L = H$, A: Input B: Output
B ^{Note}	LEFT data input	35	When $R/L = L$, A: Output B: Input
CLK	Clock input	31	Shift executed on rise
CLR	Clear input	32	L: All shift registers set to "L"
R/L	Shift control input	25	$\begin{array}{l} \text{H: Right shift mode} \\ A \rightarrow O_1 \cdots O_{40} \rightarrow B \\ \text{L: Left shift mode} \\ B \rightarrow O_{40} \cdots O_1 \rightarrow A \end{array}$
O1 to O40	High breakdown voltage output	1 to 20, 45 to 64	100 V, 150 mA MAX.
V _{DD1}	Logic block power supply	26, 39	5 V ± 10 %
V _{DD2}	Driver block power supply	21, 44, 65, 66, 79, 80	30 to 90 V
Vss1	Logic ground	24, 41,	Connected to system GND
Vss2	Driver ground	22, 23, 42, 43, 67 to 78	Connected to system GND
NC	Non-connection pins	28, 29, 33, 34, 38, 40	Non-connection

Note Data which is input to the shift registers is always inverted input data A (B) and data in the shift registers is always inverted when it is output. (Refer to the truth tables and timing chart.)

TRUTH TABLE 1 (Shift Register Block)

Ing	Input		tput	
R/L	CLK	А	В	Shift Register
Н	Ŷ	Input	Output ^{Notes 1}	Right shift executed
н	H or L		Output	Retained
L	Ŷ	Output ^{Notes 2}	Input	Left shift executed
L	H or L	Output		Retained

Notes 1. The data of internal shift register S₃₉ is shifted to S₄₀ on a rise of CLK and inverted data of S₄₀ is output from B. (Refer to the timing chart.)

The data of internal shift register S₂ is shifted to S₁ on a rise of CLK and inverted data of S₁ is output from A. (Refer to the timing chart.)

TRUTH TABLE 2 (Latch Block)

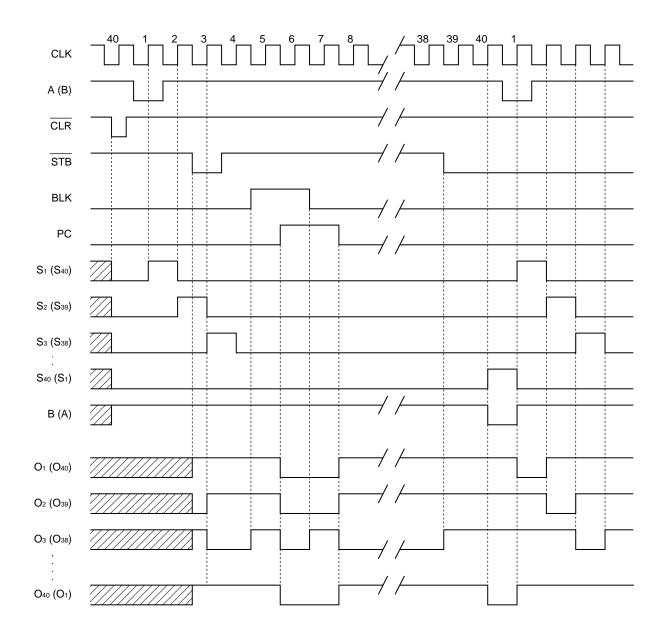
STB	Operation			
н	Retains data immediately before STB becomes H.			
L	Outputs data of shift register.			

TRUTH TABLE 3 (Driver Block)

	Inp	out		
A (B)	STB	BLK	PC	State of Driver Output
×	×	Н	Н	L (all driver outputs: L)
×	×	Н	L	H (all driver outputs: H)
L	L	L	Н	Н
L	L	L	L	L
н	L	L	Н	L
Н	L	L	L	Н
×	Н	L	Н	Outputs data of Sn on STB rise.
×	Н	L	L	Inverts and outputs data of S_n on \overline{STB} rise.

×: H or L, H: High level L: Low level

TIMING CHART



ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, Vss1 = Vss2 = 0 V)

Item	Symbol	Rating	Unit
Logic block supply voltage	V _{DD1}	– 0.5 to + 7.0	V
Driver block supply voltage	V _{DD2}	– 0.5 to + 100	V
Logic block input voltage	VI1	- 0.5 to V _{DD1} + 0.5	V
Logic block output voltage	Vo1	- 0.5 to V _{DD1} + 0.5	V
Driver block output voltage	V ₀₂	- 0.5 to V _{DD2} + 0.5	V
Driver output current	lo2	± 150 ^{Notes 1}	mA
Package power dissipation	PD	1300 ^{Notes 2}	mW
Operating ambient temperature	TA	– 20 to + 85	°C
Storage temperature	Tstg.	– 65 to + 150	°C

Notes 1. A period of driver peak output current is less than 1 μ s pulse width.

2. $T_A = 25$ °C (however, values after the chip is soldered to PWB will be TBD.) When $T_A \ge 25$ °C, load should be reduced to -13 mW/ °C.

RECOMMENDED OPERATING RANGE (TA = -20 to +85 °C, Vss1 = Vss2 = 0 V)

			-,	* - /	
Item	Symbol	MIN.	TYP.	MAX.	Unit
Logic block supply voltage	Vdd1	4.5	5.0	5.5	V
Driver block supply voltage	Vdd2	30		90	V
Input voltage, high	Vін	0.7Vdd1		Vdd1	V
Input voltage, low	VIL	0		0.2VDD1	V
Driver output current	lo			±100	mA

ELECTRICAL SPECIFICATIONS (TA = 25 °C, VDD1 = 4.5 to 5.5 V, VDD2 = 90 V, VSS1 = VSS2 = 0 V)

Item	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	А (В), Іон = –1.0 mA	0.9 Vdd1		VDD1	V
Output voltage, low	Vol1	A (B), Io∟ = 1.0 mA	0		0.1VDD1	V
Output voltage, high	Voh21	О1 to O40, Iон2 = -100 mA	70	80		V
	Voh22	О1 to O40, Iон2 = -60 mA	78	84		V
Output voltage, low	Vol21	O1 to O40, IOL2 = 100 mA		10	20	V
	Vol22	O1 to O40, IOL2 = 60 mA		6	12	V
Input leakage current	h	VI = VDD1 or VSS1			±1.0	V
Static consumption current	IDD11	Logic, $T_A = -20$ to +85 °C			100	μA
	DD12	Logic, T _A = +25 °C			10	μA
	DD21	Driver, $T_A = -20$ to +85 °C			1	mA
	DD22	Driver, T _A = +25 °C			100	μA

Item	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transmission delay time	tPHL1	$CLK \rightarrow A/B$			50	ns
	tPLH1				50	ns
	tPLH2	$\overline{\text{CLR}} \rightarrow \text{A/B}$			60	ns
	t _{PHL3}	$CLK \rightarrow O_1$ to O_{40}			200	ns
	t _{PLH3}				200	ns
	tPHL4	$\overline{\text{STB}} \rightarrow O_1 \text{ to } O_{40}$			180	ns
	tplH4				180	ns
	tPHL5	$BLK\toO_1\text{ to }O_{40}$			175	ns
	t _{PLH5}				175	ns
	tPHL6	$PC \rightarrow O_1$ to O_{40}			170	ns
	tPLH6				170	ns
Rise time O1 to O40	tтьн	C∟ = 150 pF			150	ns
Fall time O1 to O40	tтн∟	C∟ = 150 pF			150	ns
Maximum clock frequency	fmax.	Data fetch, duty = 50%	20			MHz
		With cascading, duty = 50%	16			MHz
Input capacitance	Ci				15	pF

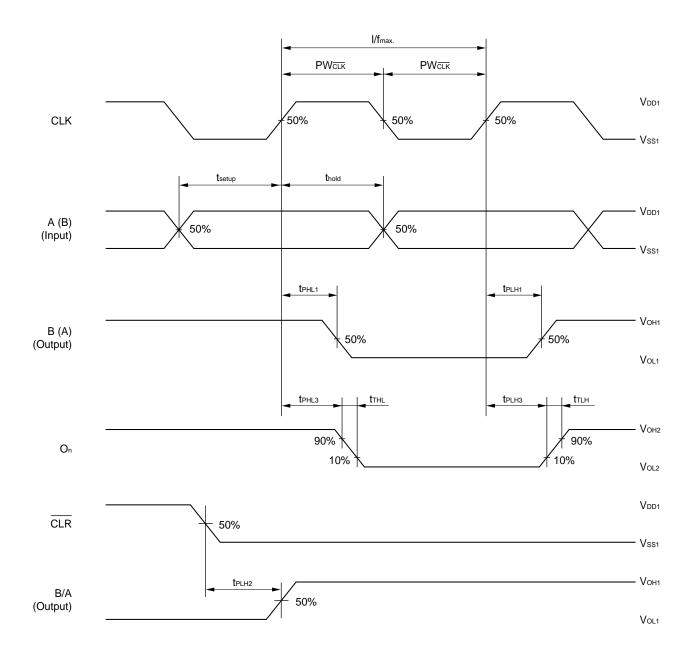
SWITCHING CHARACTERISTICS (TA = 25 °C, VDD1 = 5.0 V, VDD2 = 90 V, Logic CL = 15 pF, Driver CL = 150 pF)

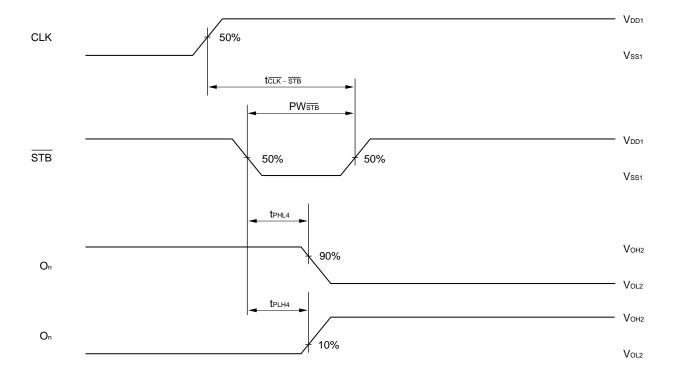
TIMING REQUIREMENTS (TA = -20 to +85 °C, VDD1 = 4.5 to 5.5 V, Vss1 = Vss2 = 0 V)

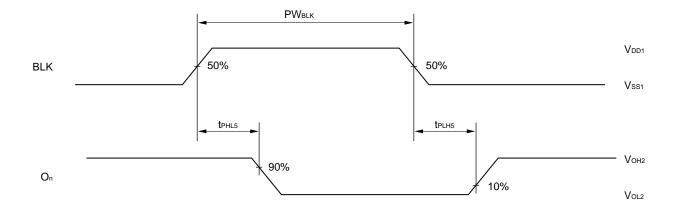
Item	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Clock pulse width	PWclk		25			ns
Strobe pulse width	PWSTB		60			ns
Blank pulse width	PWBLK		400			ns
Inverted polarity pulse width	PW _{PC}		400			ns
Clear pulse width			120			ns
Data setup time	t setup		10			ns
Data hold time	thold		10			ns
Clock-strobe time	tclk-stb	$CLK \uparrow \to \overline{STB} \uparrow$	60			ns

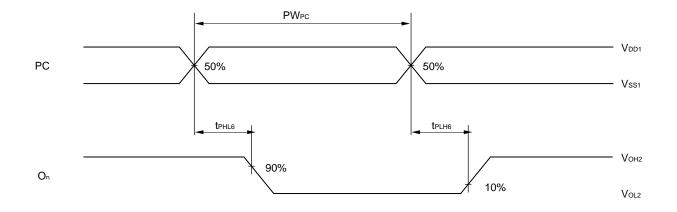
SWITCHING CHARACTERISTIC WAVEFORMS (R/L = H)

Figures in parentheses apply when $R/\overline{L} = H$.



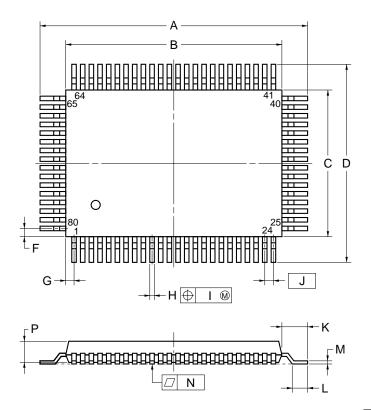


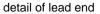


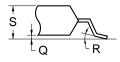


PACKAGE DRAWING

80 PIN PLASTIC QFP (14×20)







NOTE

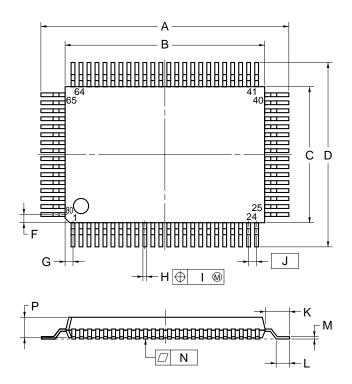
Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

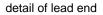
ITEM	MILLIMETERS	INCHES
А	23.6±0.4	0.929±0.016
В	20.0±0.2	$0.795^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.6±0.4	0.693±0.016
F	1.0	0.039
G	0.8	0.031
Н	0.35±0.10	$0.014^{+0.004}_{-0.005}$
I	0.15	0.006
J	0.8 (T.P.)	0.031 (T.P.)
к	1.8±0.2	$0.071^{+0.008}_{-0.009}$
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
М	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	2.7	0.106
Q	0.1±0.1	0.004±0.004
R	5°±5°	5°±5°
S	3.0 MAX.	0.119 MAX.
		P80GF-80-3B9-3

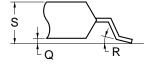
Caution Since there are two type packages which lead length is different, need designing to be able to use two packages. (note: page 10, 11)

PACKAGE DRAWING

80 PIN PLASTIC QFP (14×20)







NOTE

Each lead centerline is located within 0.15 mm (0.006 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
А	23.2±0.2	$0.913^{+0.009}_{-0.008}$
В	20.0±0.2	$0.787^{+0.009}_{-0.008}$
С	14.0±0.2	$0.551^{+0.009}_{-0.008}$
D	17.2±0.2	0.677±0.008
F	1.0	0.039
G	1.8	0.031
н	0.35±0.10	$0.014^{+0.004}_{-0.005}$
I	0.15	0.006
J	0.8 (T.P.)	0.031 (T.P.)
К	1.6±0.2	0.063±0.008
L	0.8±0.2	$0.031^{+0.009}_{-0.008}$
М	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.003}$
N	0.10	0.004
Р	2.7	0.106
Q	0.125±0.075	0.005±0.003
R	5°±5°	5°±5°
S	3.0 MAX.	0.119 MAX.
		S80GF-80-3B9-3

RECOMMENDED SOLDERING CONDITIONS

Please perform the soldered mounting of this product under the following recommended conditions.

For soldering methods and conditions other than those recommended here, please contact your NEC sales representative.

Surface Mount Type

For details on recommended soldering conditions, please refer to the "Semiconductor Device Mounting Technology Manual" (C10535E).

μ**PD16306AGF-3BA**

Soldering Method	Soldering Conditions	Recommended Conditions Symbol
Infrared Reflow	Package peak temperature: 235 °C, time: up to 30 sec. (no less than 210 °C), count: twice, restricted number of days: less than 7 days ^{Note}	IR-35-207-2
VPS	Package peak temperature: 215 °C, time: up to 40 sec. (no less than 200 °C), count: once, restricted number of days: less than 7 days ^{Note}	VP15-207-1
Pin Part Heating	Pin part temperature: no more than 300 °C, time: up to 10 sec., restricted number of days: none ^{Note}	

Note This refers to the restricted number of days for storage after decapsulating the dry pack. The storage conditions are no more than 25 °C and 65 % RH.

Caution Please avoid mixing use of soldering methods (except for pin part heating methods).

References

NEC Semiconductor Device Reliability/Quality Control System (IEI-1212) Quality Grades of NEC Semiconductor Devices (C11531E) Semiconductor Device Mounting Technology Manual (C10535E) [MEMO]

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